

MA707

Silicon epitaxial planer type

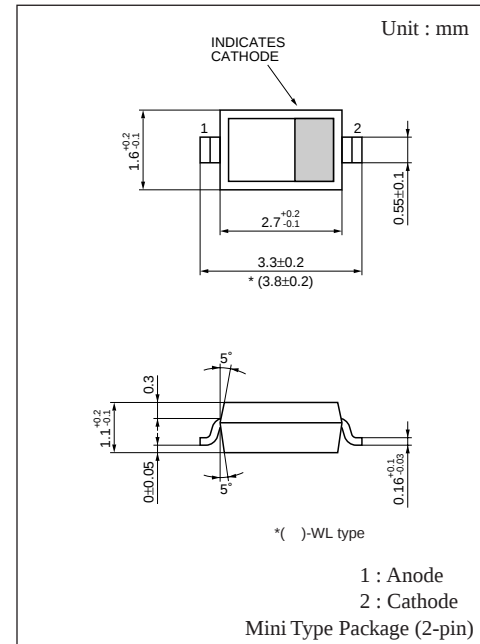
For UHF mixer

■ Features

- Small forward voltage V_F
- Large conversion gain GC and optimum for UHF mixer
- Mini package, enabling down-sizing of the equipment and automatic insertion through taping

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	5	V
Forward voltage	V_F	0.5	V
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	- 55 to + 125	°C



Marking Symbol : 5B

■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Forward current (DC)	I_F	$V_F = 0.5V$	35		100	mA
Reverse current (DC)	I_R	$V_R = 5V$			35	μA
Forward voltage (DC)	V_F	$I_F = 2mA$		0.25		V
Reverse yield voltage (DC)	$V_{(BR)R}$	$I_R = 1mA$	5			V
Terminal capacitance	C_t	$V_R = 0.5V, f = 1MHz$	0.65	0.85	1.05	pF
Conversion gain	GC*1, 2	$R_F = 890MHz, L_O = 935MHz, I_F = 45MHz$	- 7	- 5		dB
Static breakdown strength		$C = 100pF$ Breakdown judgment point $I_R \geq 35\mu A$	100	200		V

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Noise index is 8.5dB.

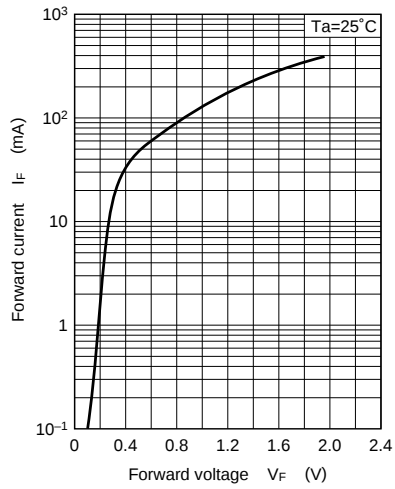
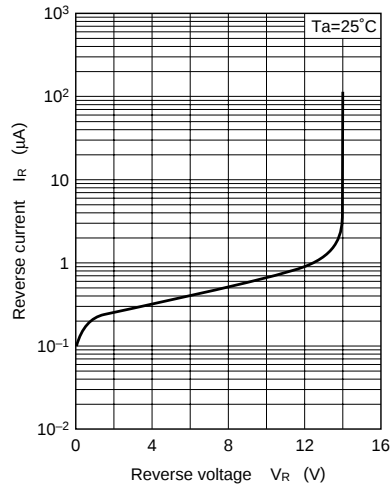
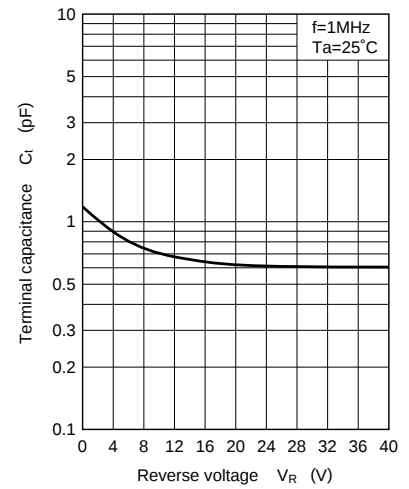
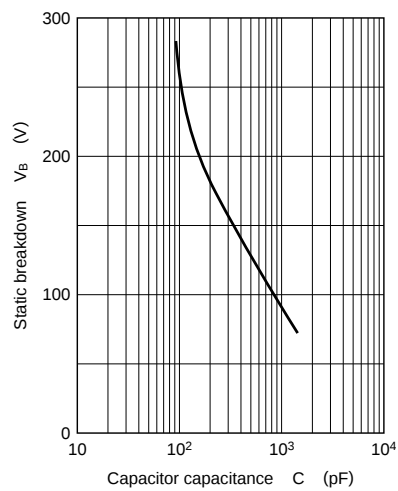
3. Rated input/output frequency : 935MHz

4. *1 Judgement is to be made per each chip lot. Sampling of LTPD= 20% and n=11 is guaranteed.

*2 GC= -7dB min. Any substandard product will be negotiated by both parties.

■ Marking



$I_F - V_F$  $I_R - V_R$  $C_t - V_R$  $V_B - C$  $GC - P_{\text{LOC}}$ 